MITSUBISHI ELECTRIC

<IGBT Modules>

CM800DW-34T

HIGH POWER SWITCHING USE
INSULATED TYPE

Collector current I_C ..... **800** A
Collector-emitter voltage V_{CES} ..... **1700** V
Maximum junction temperature T_{vjmax} ..... **175** °C

- Dual switch (Half-bridge)
- Copper base plate (Nickel-plating)
- Ni-plating signal terminals
- RoHS Directive compliant
- UL Recognized under UL1557, File No. E323585

APPLICATION

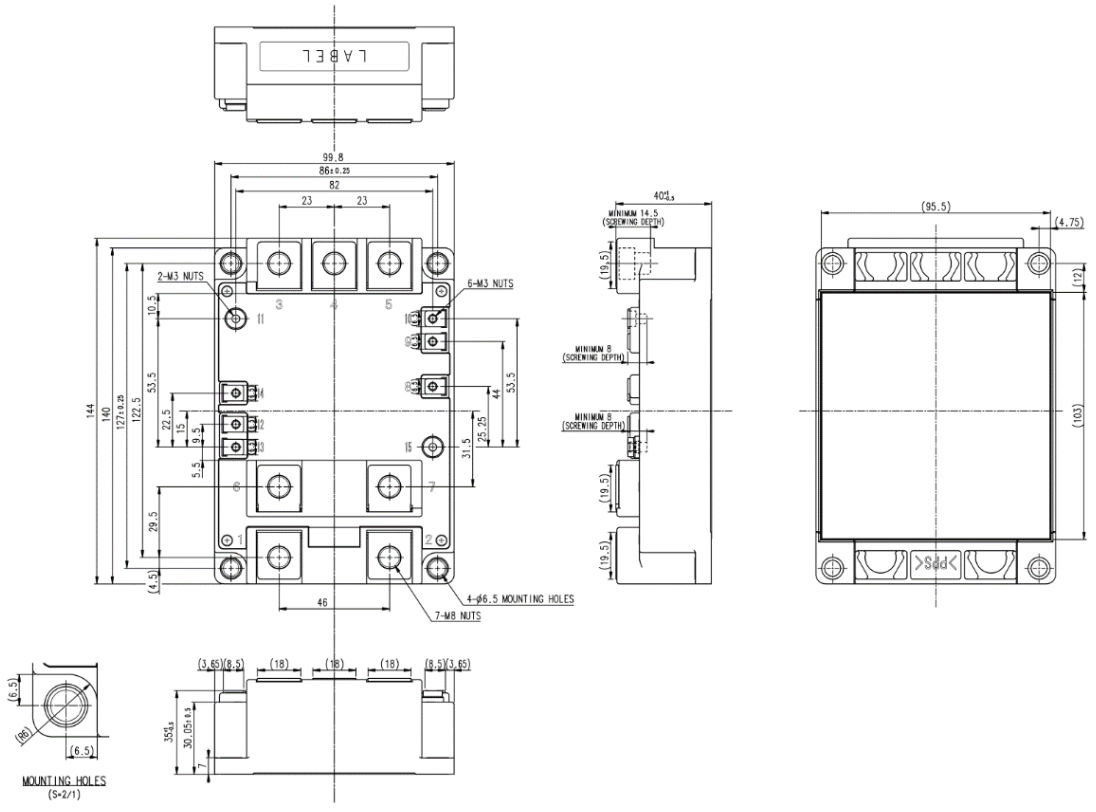
AC motor control, Wind power, etc.

OPTION (Below options are available)

- PC-TIM (Phase Change Thermal Interface Material) pre-apply
- V_{CEsat} selection for parallel connection

OUTLINE DRAWING & INTERNAL CONNECTION

Dimension in mm



Tolerance otherwise specified

Division of Dimension		Tolerance
0.5	to 3	±0.2
over 3	to 6	±0.3
over 6	to 30	±0.5
over 30	to 120	±0.8
over 120	to 400	±1.2

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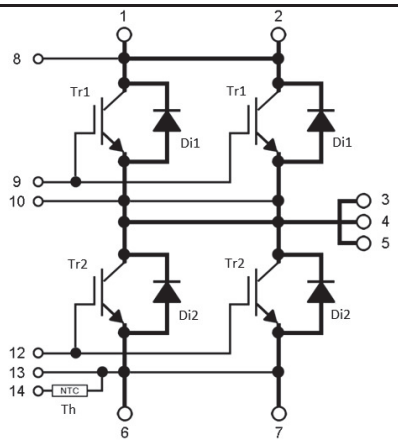
<IGBT Modules>

CM800DW-34T

HIGH POWER SWITCHING USE
INSULATED TYPE

INTERNAL CONNECTION

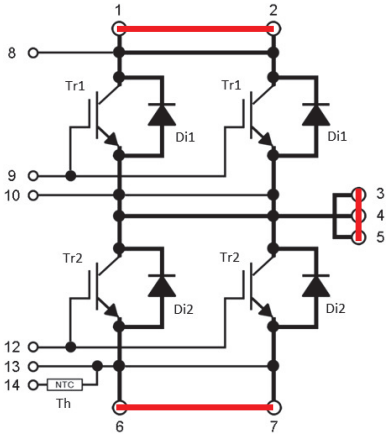


TERMINAL CODE

1. C1	9. G1
2. C1	10. Es1
3. C2E1	11. NC
4. C2E1	12. G2
5. C2E1	13. Es2, TH2
6. E2	14. TH1
7. E2	15. NC
8. Cs	

NOTE

Terminal 1 and 2, Terminal 3,4 and 5, Terminal 6 and 7,
These terminals should be connected respectively when it is used.



CM800DW-34T

HIGH POWER SWITCHING USE
INSULATED TYPE

MAXIMUM RATINGS (T_{vj}=25 °C, unless otherwise specified)

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	1700	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I_C	Collector current	DC, T_C=72°C (Note2, 4)	800	A
I_{CRM}		Pulse, Repetitive (Note3)	1600	
P_{tot}	Total power dissipation	T_C=25 °C (Note2, 4)	3655	W
I_E (Note1)	Emitter current	DC (Note2)	800	A
I_{ERM} (Note1)		Pulse, Repetitive (Note3)	1600	
V_{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	4000	V
$T_{vj\,max}$	Maximum junction temperature	Instantaneous event (overload) (Note9)	175	°C
$T_{c\,max}$	Maximum case temperature	(Note4, 9)	125	°C
$T_{vj\,op}$	Operating junction temperature	Continuous operation (Note9)	-40 ~ +150	°C
T_{stg}	Storage temperature	-	-40 ~ +125	

ELECTRICAL CHARACTERISTICS (T_{vj}=25 °C, unless otherwise specified)

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
I_{CES}	Collector-emitter cut-off current	V_{CE}=V_{CES}, G-E short-circuited		-	-	1.0	mA
I_{GES}	Gate-emitter leakage current	V_{GE}=V_{GES}, C-E short-circuited		-	-	0.5	μA
$V_{GE(th)}$	Gate-emitter threshold voltage	I_C=80 mA, V_{CE}=10 V		5.4	6	6.6	V
V_{CEsat}	Collector-emitter saturation voltage	I_C=800 A (Note5)	T_{vj}=25 °C	-	2.00	2.40	V
		V_{GE}=15 V,	T_{vj}=125 °C	-	2.40	-	
		(Terminal)	T_{vj}=150 °C	-	2.50	-	
		I_C=800 A (Note5)	T_{vj}=25 °C	-	1.95	2.35	V
		V_{GE}=15 V,	T_{vj}=125 °C	-	2.35	-	
		(Chip)	T_{vj}=150 °C	-	2.45	-	
C_{ies}	Input capacitance	V_{CE}=10 V, V_{GE}=0V		-	-	220	nF
C_{oes}	Output capacitance			-	-	5.8	
C_{res}	Reverse transfer capacitance			-	-	1.9	
Q_G	Gate charge	V_{CC}=1000 V, I_C=800 A, V_{GE}=15 V		-	6.3	-	μC
$t_{d(on)}$	Turn-on delay time	V_{CC}=1000 V, I_E=800 A, V_{GE}=±15 V,		-	-	800	ns
t_r	Rise time			-	-	200	
$t_{d(off)}$	Turn-off delay time	R_G=0 Ω, Inductive load		-	-	800	
t_f	Fall time			-	-	600	
V_{EC} (Note1)	Emitter-collector voltage	I_E=800 A(Note5)	T_{vj}=25 °C	-	2.70	3.30	V
		G-E short-circuited	T_{vj}=125 °C	-	2.80	-	
		(Terminal)	T_{vj}=150 °C	-	2.80	-	
		I_E=800 A(Note5),	T_{vj}=25 °C	-	2.65	3.25	V
		G-E short-circuited,	T_{vj}=125 °C	-	2.75	-	
		(Chip)	T_{vj}=150 °C	-	2.75	-	
t_{rr} (Note1)	Reverse recovery time	V_{CC}=1000 V, I_E=800 A, V_{GE}=±15 V,		-	-	300	ns
Q_{rr} (Note1)	Reverse recovery charge	R_G=0 Ω, Inductive load		-	48	-	μC
E_{on}	Turn-on switching energy per pulse	V_{CC}=1000V, I_C=I_E=800A,		-	115	-	mJ
E_{off}	Turn-off switching energy per pulse	V_{GE}=±15V, R_G=0Ω, T_{vj}=150°C,		-	202	-	
E_{rr} (Note1)	Reverse recovery energy per pulse	Inductive loard		-	136	-	
$R_{CC'+EE'}$	Internal lead resistance	Main terminals-chip Tc=25°C (Note4)		-	0.25	-	mΩ
r_g	Internal gate resistance	Per switch		-	1.0	-	Ω

NTC THERMISTOR PART

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R_{25}	Zero-power resistance	T_C=25 °C (Note4)	4.85	5.00	5.15	kΩ
ΔR/R	Deviation of resistance	R_{100}=493 Ω, T_C=100 °C (Note4)	-7.3	-	+7.8	%
$B_{(25/50)}$	B-constant	Approximate by equation (Note6)	-	3375	-	K
P_{25}	Power dissipation	T_C=25 °C (Note4)	-	-	10	mW

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal resistance	Junction to case, per IGBT switch (Note4)	-	-	41	K/kW
$R_{th(j-c)D}$		Junction to case, per FWD switch (Note4)	-	-	59	
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, per 1 module, Thermal grease applied (Note 4,7,9)	-	10	-	K/kW

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
M_t	Mounting torque	Main terminals	M 8 screw	7.0	10.5	14.0	N·m
M_s		Mounting to heat sink	M 6 screw	3.5	4.0	4.5	
M_t		Auxiliary terminals	M 3 screw	0.4	0.5	0.6	
d_s	Creepage distance	Terminal to terminal		17	-	-	mm
		Terminal to base plate		30	-	-	
d_a	Clearance	Terminal to terminal		8.5	-	-	mm
		Terminal to vase plate		28	-	-	
e_c	Flatness of base plate	On the centerline X, Y (Note8)		0	-	+200	μm
m	mass	-		-	860	-	g

*: This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU and (EU)2015/863.

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free-wheeling diode (FWD).

2. Junction temperature (T_{vj}) should not increase beyond T_{vjmax} rating.

3. Pulse width and repetition rate should be such that the device junction temperature (T_{vj}) dose not exceed T_{vjmax} rating.

4. Case temperature (T_C) and heat sink temperature (T_S) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.

5. Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.

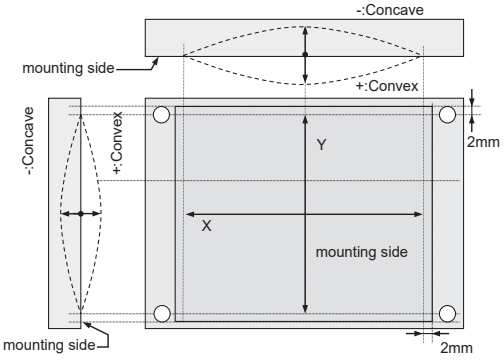
6. $B(25/50) - \ln(\frac{R_{25}}{R_{50}}) / (\frac{1}{T_{25}} - \frac{1}{T_{50}})$

   R_{25}: resistance at absolute temperature T_{25} [K]; T_{25}=25 [°C]+273.15=298.15 [K]

   R_{50}: resistance at absolute temperature T_{50} [K]; T_{50}=50 [°C]+273.15=323.15 [K]

7. Reference value. Thermally conductive grease of thermal conductivity λ=0.9 W/(m·K) and thickness D(C-S)=50 μm.

8. The base plate (mounting side) flatness measurement points (X, Y) are shown in the following figure.



9. Long term performance related to thermal conductive grease (including but not limited to aspects such as the increase of thermal resistance due to pumping out, etc.) should be verified under user's specific application conditions. Each temperature condition ($T_{vj\,max}$, $T_{vj\,op}$, $T_{C\,max}$) must be maintained below the maximum rated temperature throughout consideration of the temperature rise even for long term usage.

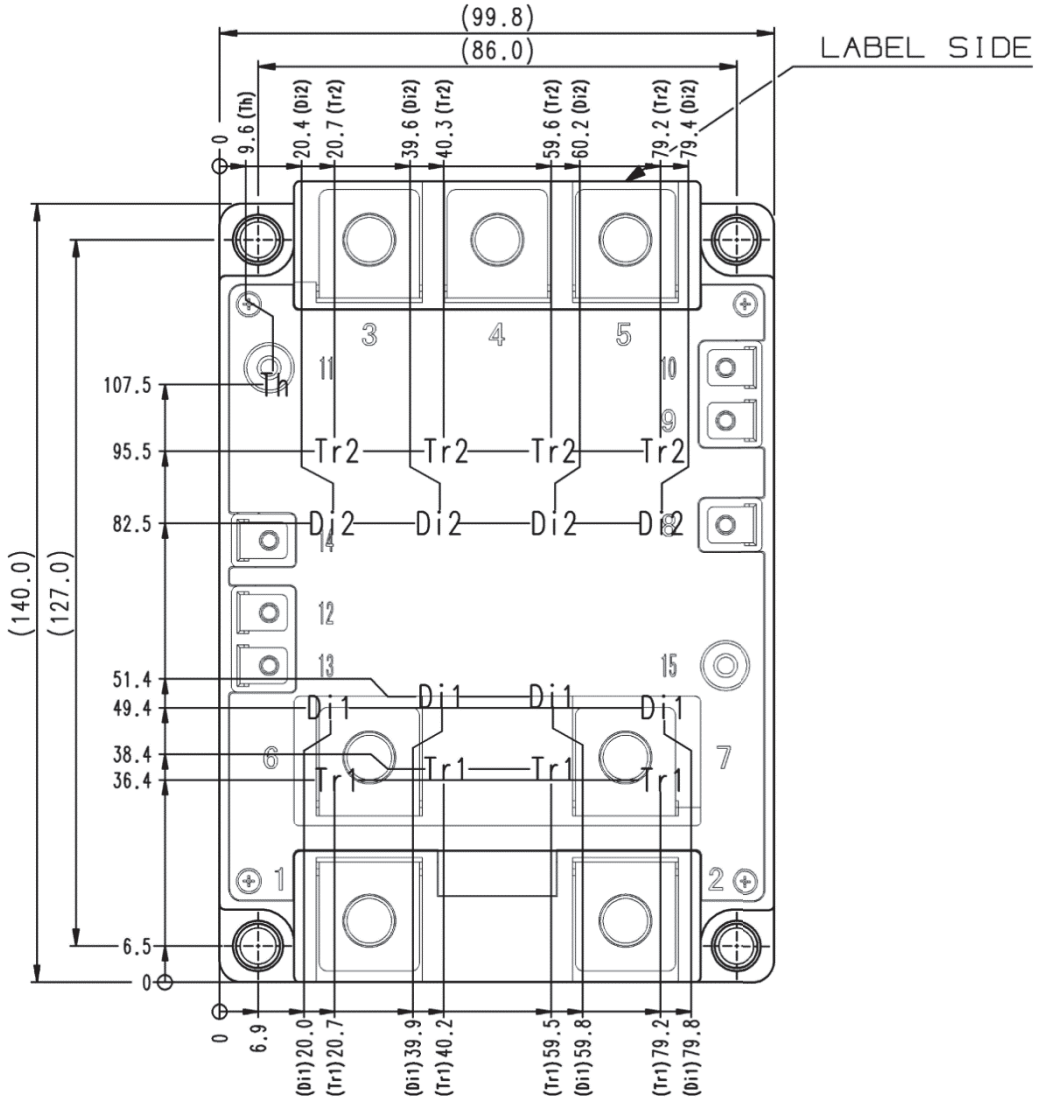
RECOMMENDED OPERATING CONDITIONS

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
V_{CC}	(DC) Supply voltage	Applied across C1-E2 terminals		-	1000	1200	V
V_{GEon}	Gate-emitter drive voltage	Applied across G1-Es1/G2-Es2 terminals		13.5	15.0	16.5	V
R_G	External gate resistance	Per switch	on	0	-	10	Ω
			off	0	-	15	Ω

Optimum operating conditions should be selected with careful confirmation for no occurrence of any maximum rating violation (T_{vj}, V_{CES}, etc.) or any unexpected malfunction (arm-short-through, oscillation, etc.) at the actual application conditions.

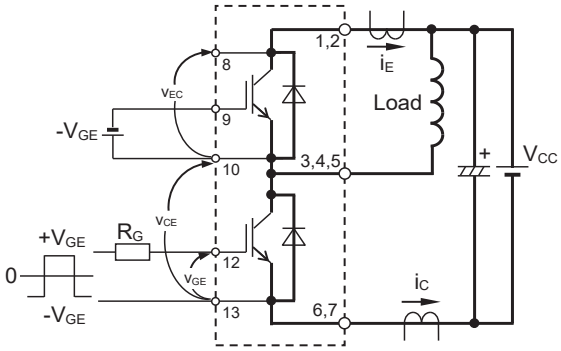
CHIP LOCATION (Top view)

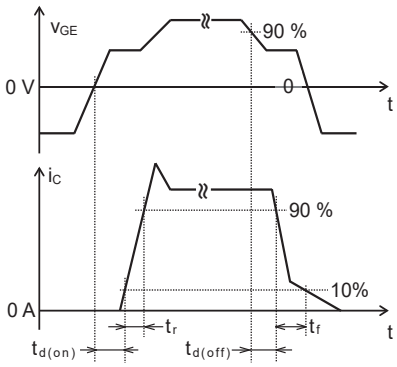
Dimension in mm, tolerance: ±1 mm



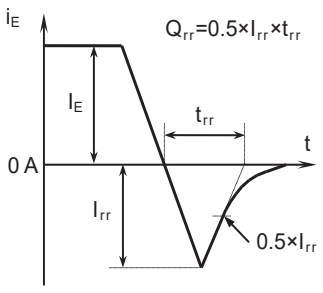
Tr1/Tr2: IGBT, Di1/Di2: FWD, Th: NTC thermistor

TEST CIRCUIT AND WAVEFORMS

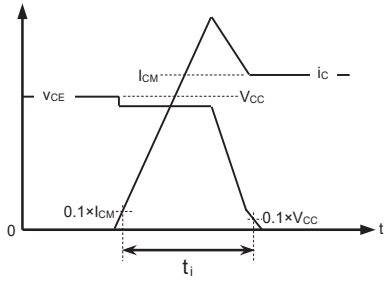




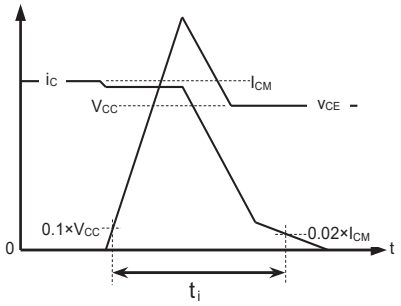
Switching characteristics test circuit and waveforms



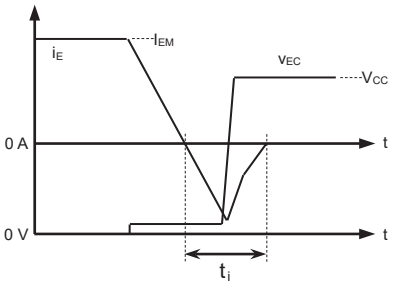
t_{rr}, Q_{rr} characteristics test waveform



IGBT Turn-on switching energy



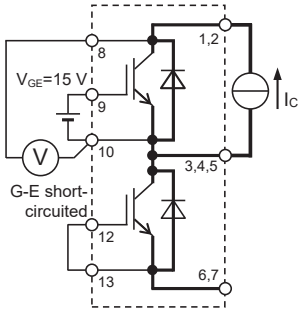
IGBT Turn-off switching energy



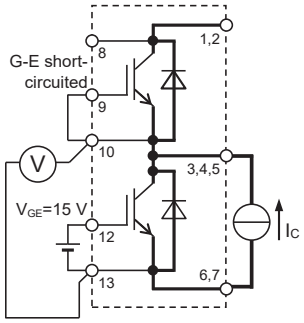
FWD Reverse recovery energy

Switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

TEST CIRCUIT

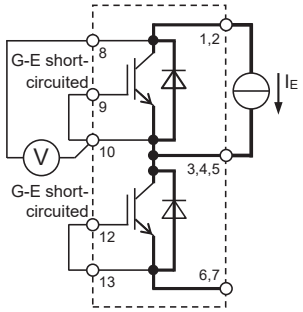


Tr1

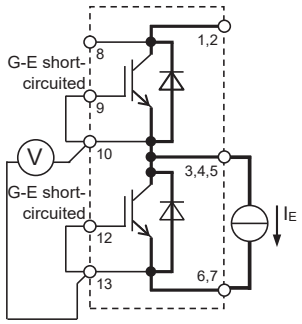


Tr2

V_{CEsat} characteristics test circuit



Di1



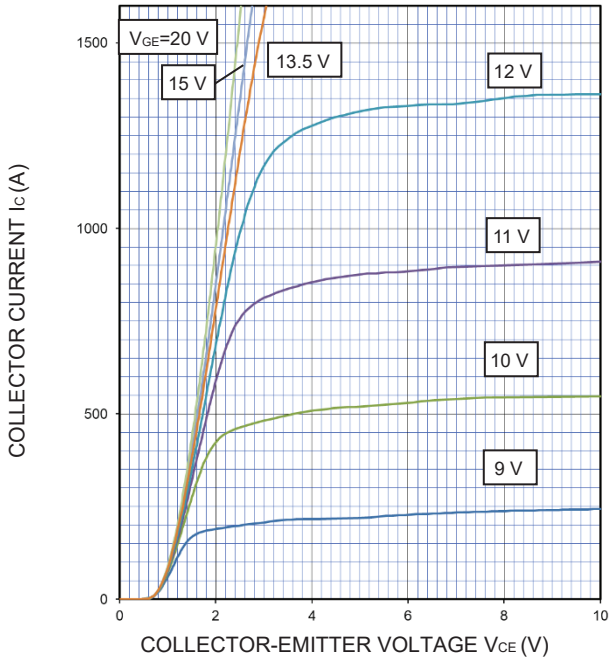
Di2

V_{EC} characteristics test circuit

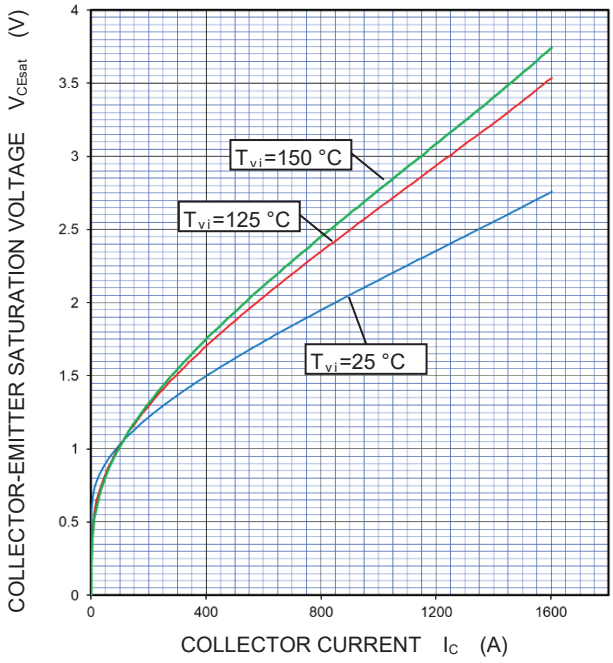
PERFORMANCE CURVES

INVERTER PART

OUTPUT CHARACTERISTICS
(TYPICAL)
T_{vj}=25°C (chip)

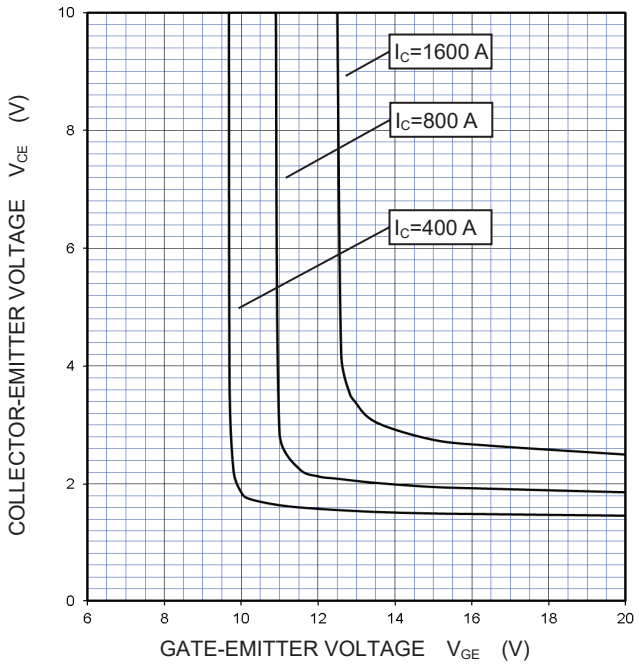


COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)
V_{GE}=15V (chip)

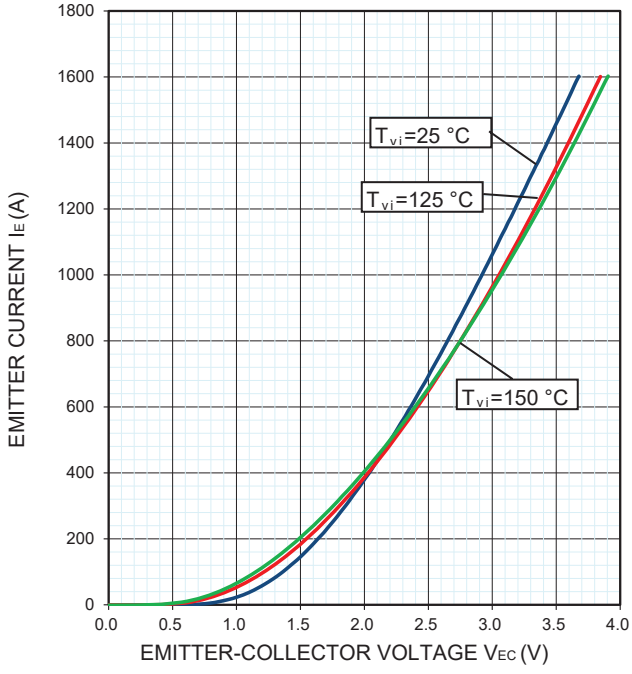


COLLECTOR-EMITTER VOLTAGE CHARACTERISTICS (TYPICAL)

T_{vj}=25°C (chip)



FREE WHEELING DIODE FORWARD CHARACTERISTICS (TYPICAL)
G-E short-circuited (chip)

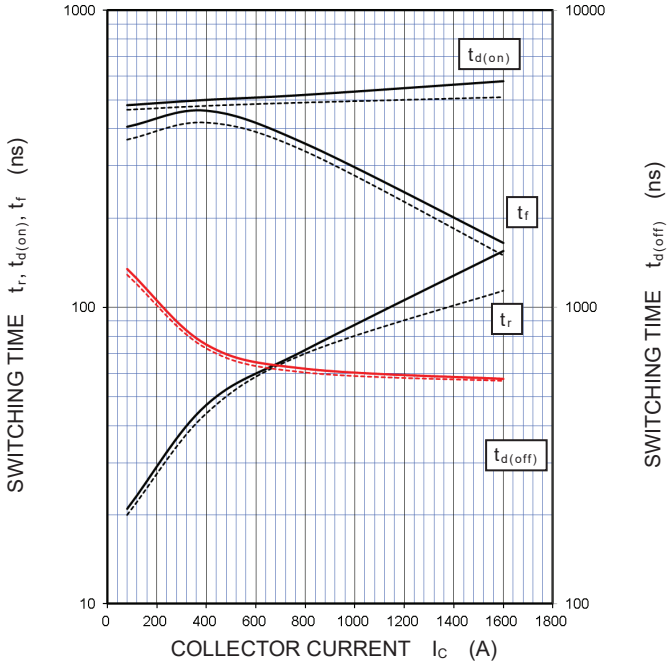


PERFORMANCE CURVES

INVERTER PART

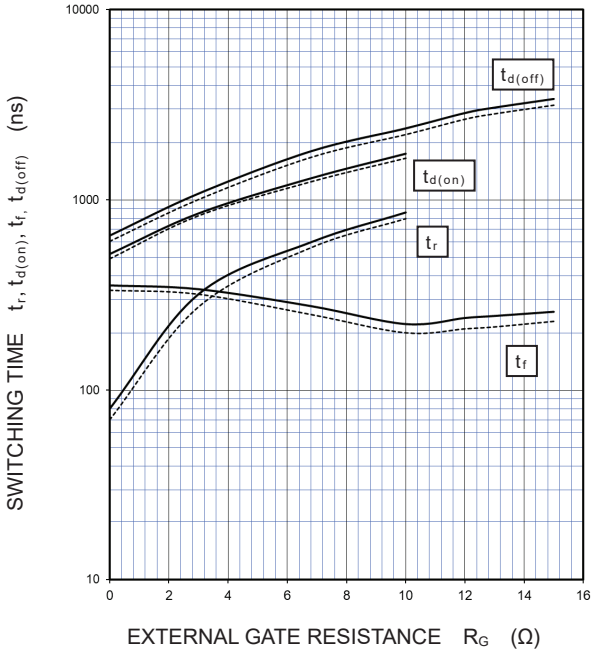
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

V_{CC}=1000 V, R_G=0 Ω, V_{GE}=±15 V, INDUCTIVE LOAD
————: T_{vj}=150 °C, - - - - -: T_{vj}=125 °C



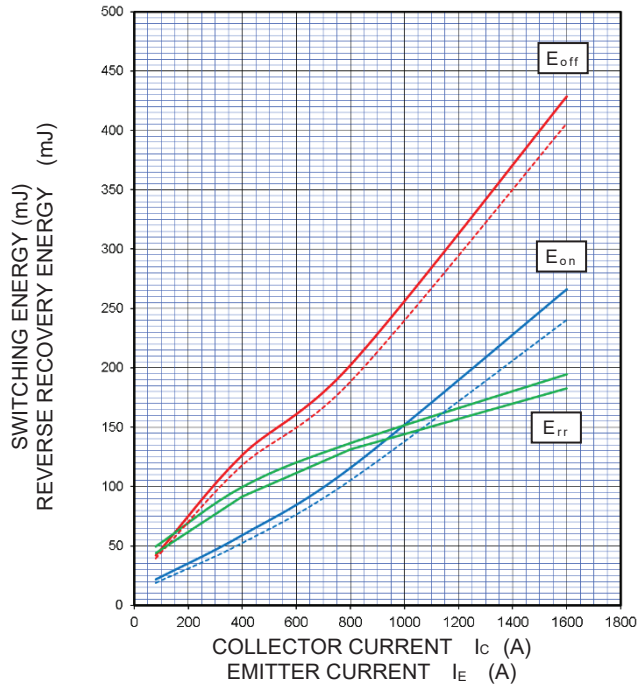
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

V_{CC}=1000 V, I_C=800 A, V_{GE}=±15 V, INDUCTIVE LOAD
————: T_{vj}=150 °C, - - - - -: T_{vj}=125 °C



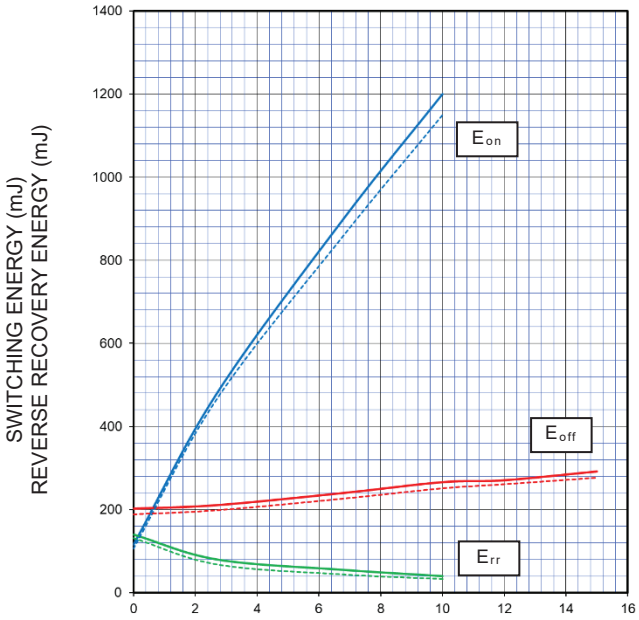
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

V_{CC}=1000 V, R_G=0 Ω, V_{GE}=±15 V, INDUCTIVE LOAD
—— : T_{vj}=150 °C, - - -: T_{vj}=125 °C,
PER PULSE



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

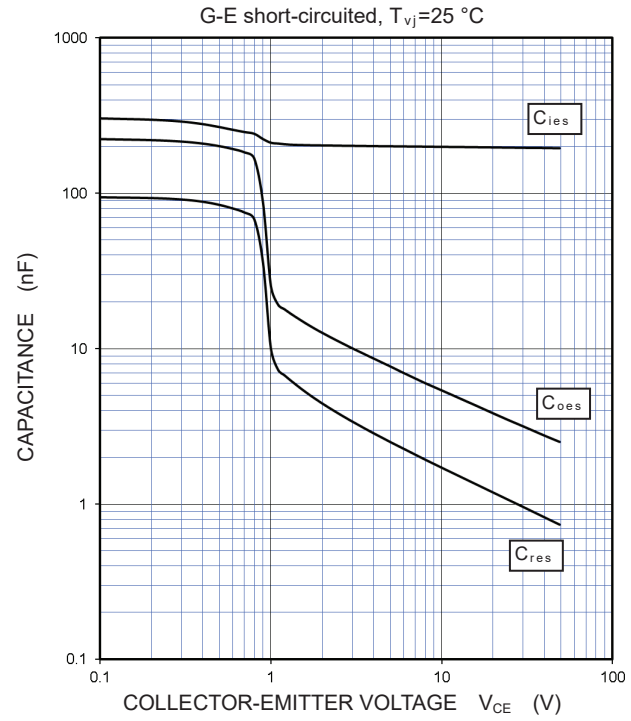
V_{CC}=1000 V, I_C/I_E=800 A, V_{GE}=±15 V, INDUCTIVE LOAD,
—— : T_{vj}=150 °C, - - -: T_{vj}=125 °C,
PER PULSE



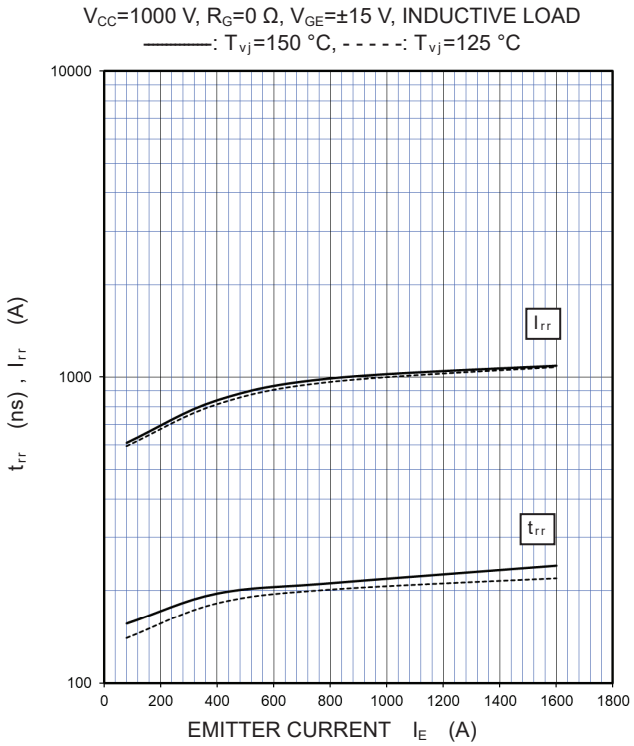
PERFORMANCE CURVES

INVERTER PART

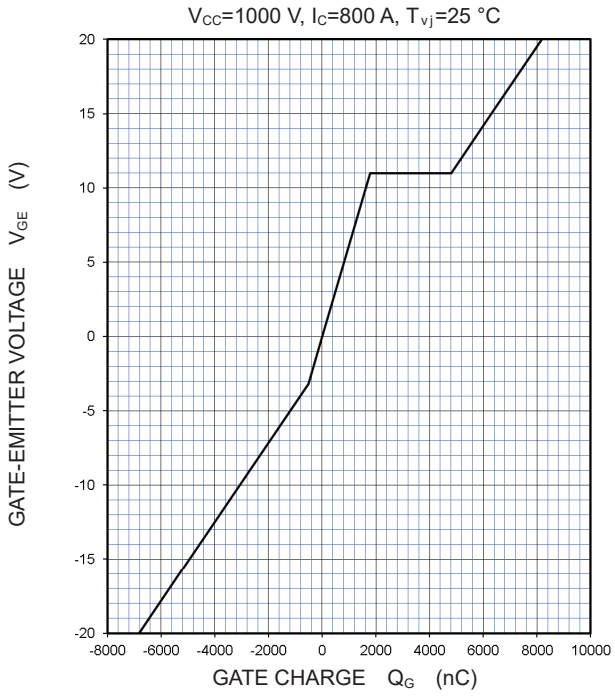
CAPACITANCE CHARACTERISTICS (TYPICAL)



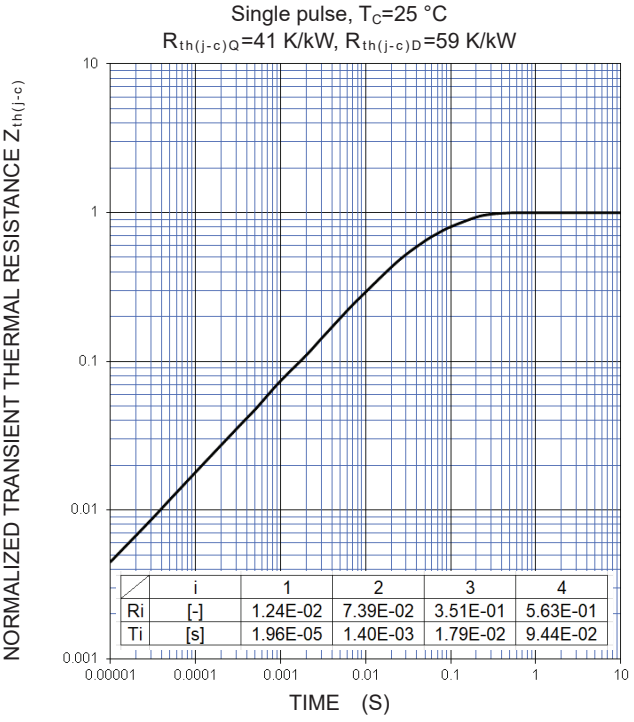
FREE WHEELING DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



GATE CHARGE CHARACTERISTICS (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)

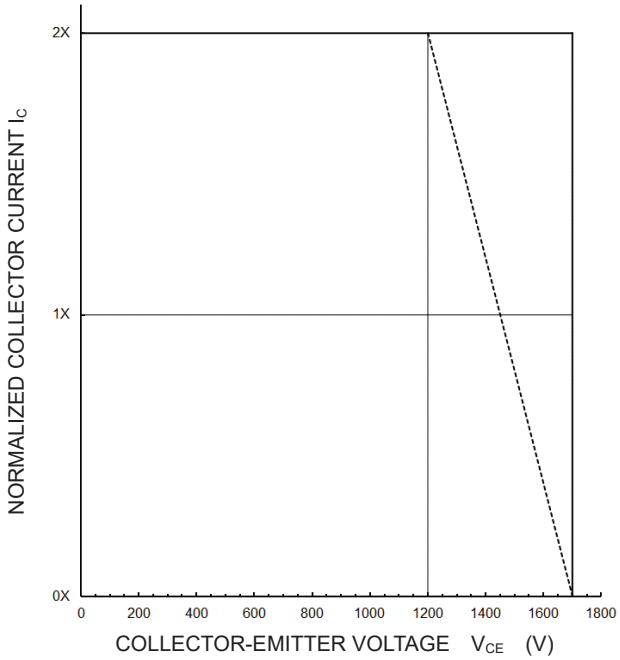


i	1	2	3	4
Ri [-]	1.24E-02	7.39E-02	3.51E-01	5.63E-01
Ti [s]	1.96E-05	1.40E-03	1.79E-02	9.44E-02

PERFORMANCE CURVES

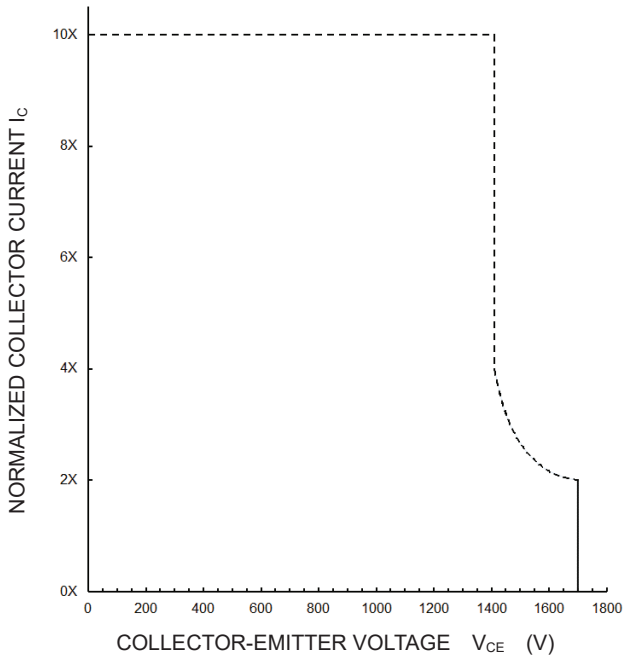
TURN-OFF SWITCHING SAFE OPERATIONG AREA (REVERSE BIAS SAFE OPERATING AREA) (MAXIMUM)

V_{CC}≤1200 V, V_{GE}=±15 V, $R_{G(off)}$=0~15 Ω,
————: T_{vj}=25~150 °C (Normal load operations (Continuous)
- - - - - -: T_{vj}=175 °C (Unusual load operations (Limited period)



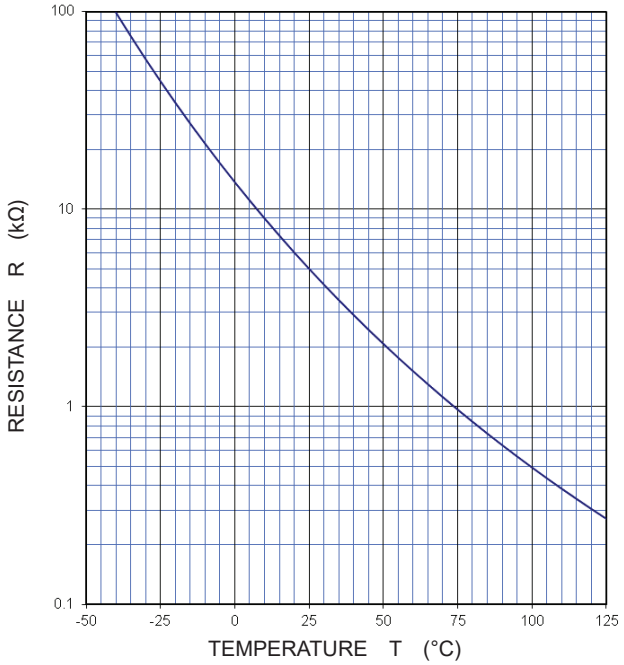
SHORT-CIRCUIT SAFE OPERATING AREA (MAXIMUM)

V_{CC}≤1200 V, V_{GE}=±15 V,
T_{vj}= 25 ~ 150 °C, t_W≤8 μs, Non-Repetitive



NTC thermistor part

TEMPERATURE CHARACTERISTICS (TYPICAL)



Note: The characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Important Notice

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